L	Hits	Search Text	DB	Time stamp
Number				
1	31025	semiconductor and ((thin adj film adj	USPAT;	2004/10/07
		transistor) or tft)	US-PGPUB;	10:39
			EPO; JPO;	
			DERWENT;	
]	11501		IBM_TDB	0004/10/07
2	11501	(semiconductor and ((thin adj film adj	USPAT;	2004/10/07
		transistor) or tft)) and (amorphous adj (silicon or si))	US-PGPUB; EPO; JPO;	10:40
		(SIIICOII OI SI))	DERWENT;	
			IBM TDB	
3	7059	((semiconductor and ((thin adj film adj	USPAT;	2004/10/07
	, , , ,	transistor) or tft)) and (amorphous adj	US-PGPUB;	10:40
		(silicon or si))) and plurality	EPO; JPO;	
1		(*************************************	DERWENT;	
			IBM TDB	
4	2600	(((semiconductor and ((thin adj film adj	USPĀT;	2004/10/07
		transistor) or tft)) and (amorphous adj	US-PGPUB;	10:41
		(silicon or si))) and plurality) and	EPO; JPO;	
		island	DERWENT;	
			IBM_TDB	
5	1241	((((semiconductor and ((thin adj film adj	USPAT;	2004/10/07
		transistor) or tft)) and (amorphous adj	US-PGPUB;	10:42
		(silicon or si))) and plurality) and	EPO; JPO;	
		island) and (space or cavity or recess\$2	DERWENT;	
6	1235	or groove or trench\$2) (((((semiconductor and ((thin adj film	IBM_TDB USPAT;	2004/10/07
٥	1235	adj transistor) or tft)) and (amorphous	US-PGPUB;	10:42
		adj (silicon or si))) and plurality) and	EPO; JPO;	10.42
		island) and (space or cavity or recess\$2	DERWENT;	
		or groove or trench\$2)) and substrate	IBM TDB	
7	733		USPAT;	2004/10/07
1	'**	adj transistor) or tft)) and (amorphous	US-PGPUB;	10:43
		adj (silicon or si))) and plurality) and	EPO; JPO;	
		island) and (space or cavity or recess\$2	DERWENT;	
		or groove or trench\$2)) and substrate)	IBM_TDB	
		and crystalliz\$5	_	
8	573	((((((semiconductor and ((thin adj film	USPAT;	2004/10/07
		adj transistor) or tft)) and (amorphous	US-PGPUB;	10:43
		adj (silicon or si))) and plurality) and	EPO; JPO;	
		island) and (space or cavity or recess\$2	DERWENT;	
		or groove or trench\$2)) and substrate)	IBM_TDB	
		and crystalliz\$5) and irradiat\$3 and laser		
9	544	laser (((((((semiconductor and ((thin adj film	USPAT;	2004/10/07
		adj transistor) or tft)) and (amorphous	US-PGPUB;	10:44
		adj (silicon or si))) and plurality) and	EPO; JPO;	
		island) and (space or cavity or recess\$2	DERWENT;	
<u> </u>		or groove or trench\$2)) and substrate)	IBM_TDB	
		and crystalliz\$5) and irradiat\$3 and	_	
		laser) and gate and source and drain and		
		channel		
10	461	1 , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/10/07
İ '		film adj transistor) or tft)) and	US-PGPUB;	10:47
		(amorphous adj (silicon or si))) and	EPO; JPO;	
1		plurality) and island) and (space or	DERWENT;	
		cavity or recess\$2 or groove or	IBM_TDB	
		trench\$2)) and substrate) and		
1	<u> </u>	crystalliz\$5) and irradiat\$3 and laser) and gate and source and drain and		
		channel) and (polysilicon or		
.		(polycrystal\$4 adj (silicon or si)))		
	L	1 /2-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1	I	L